54. The device of claim 44 wherein said active matrix circuit comprises a MIM diode.

55. The device of claim 44 wherein said resin material comprises a material selected from the group consisting of an epoxy resin and an ultraviolet hardening resin.

56. An electro-optical device comprising:

a first substrate;

an active matrix circuit having a plurality of pixels arranged in a matrix form on said first substrate;

at least one first driver circuit for driving said active matrix circuit on said first substrate, there being at least one side of said first substrate at which no first driver circuit is disposed and each of said active matrix circuit and said first driver circuit comprising thin film transistors provided on said first substrate;

a second substrate opposed to said first substrate wherein a second driver circuit is provided on the second substrate at a region opposed to the first driver circuit;

a liquid crystal provided between said first substrate and said second substrate;

a sealing member provided between said first substrate and said second substrate for sealing said liquid crystal therebetween, said sealing member enclosing said active matrix circuit and said first driver circuit;

an inlet for injecting said liquid crystal between said first substrate and said second substrate,

wherein said inlet is provided to said sealing member and on a side edge of said first substrate and said second substrate corresponding to said one side of said first substrate.

57. The device of claim 56 wherein the thin film transistors of each of said active matrix circuit and said first driver circuit are formed on said first substrate through a common process.